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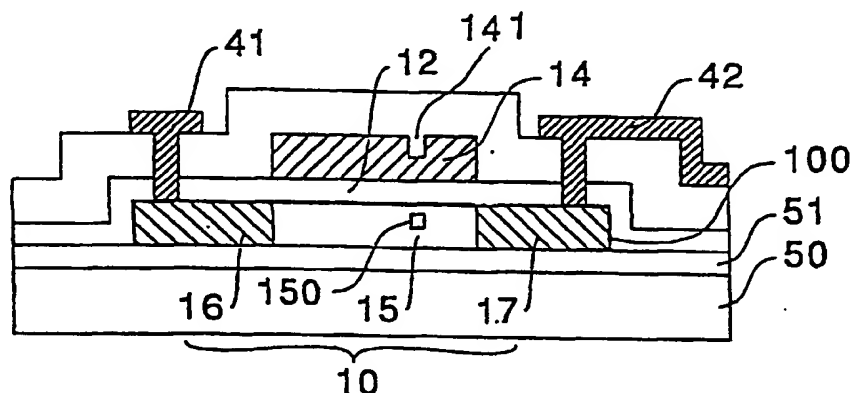
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(54) Title: METHOD OF MANUFACTURING A THIN-FILM TRANSISTOR



(57) Abstract: In a TFT 10, a channel region (15) facing a gate electrode 14 through a gate insulating film (12), a source electrode (16) connected to the channel region (15) and a drain region (17) connected to the channel region (15) on the side opposite this source region (16) are formed in a polycrystal semiconductor film (100) that was patterned in island forms. In the channel region (15), a recombination center (150) is formed for capturing a small number of carriers (holes) by introducing impurities such as inert gases, metals, Group III elements, Group IV elements and Group V elements after a crystallization process is carried out on a semiconductor film (100). The invention thus provides an arrangement restraining bipolar transistor type behavior, to stabilize saturation current and to provide a TFT that can improve reliability.

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